MC74LCX07

Advance Information

Low-Voltage CMOS Hex Buffer with Open Drain Outputs and 5V-Tolerant Inputs

The MC74LCX07 is a high performance hex buffer with open drain outputs operating from a 2.3 to 5.5 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers. Open drain outputs provide the ability to set output levels, or to do active–HIGH AND functions or active–LOW OR functions. A V_I specification of 5.5 V allows MC74LCX04 inputs to be safely driven from 5 V devices.

Current drive capability is 24mA at the outputs.

- Designed for 2.3 to 5.5 V V_{CC} Operation
- 5 V Tolerant Inputs — Interface Capability With 5 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500mA
- ESD Performance: Human Body Model >2000V; Machine Model >200V

This document contains information on a new product. Specifications and information herein are subject to change without notice.

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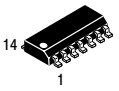
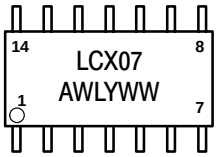
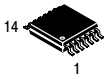
MARKING DIAGRAMS

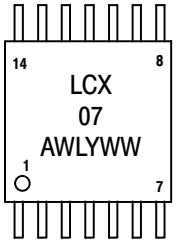


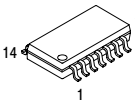
SOIC–14
D SUFFIX
CASE 751A



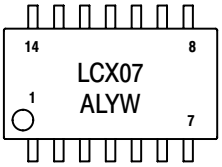


TSSOP–14
DT SUFFIX
CASE 948G





SOIC EIAJ–14
M SUFFIX
CASE 965



A =Assembly Location
WL or L = Wafer Lot
Y = Year
WW or W = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74LCX07D	SOIC–14	55 Units/Rail
MC74LCX07DR2	SOIC–14	2500 Units/Reel
MC74LCX07DT	TSSOP–14	96 Units/Rail
MC74LCX07DTR2	TSSOP–14	2500 Units/Reel
MC74LCX07M	SOIC EIAJ–14	50 Units/Rail
MC74LCX07MEL	SOIC EIAJ–14	2000 Units/Reel

Pinout: 14–Lead (Top View)

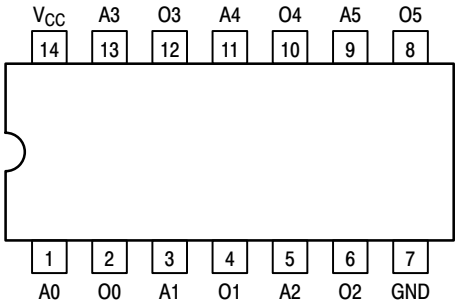
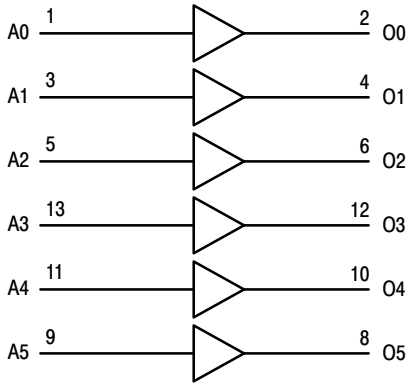


Figure 1. LOGIC DIAGRAM



PIN NAMES

Pins	Function
An	Data Inputs
On	Outputs

FUNCTION TABLE

An	On
L	L
H	Z

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V_{CC}	DC Supply Voltage	–0.5 to +7.0		V
V_I	DC Input Voltage	$–0.5 \le V_I \le +7.0$		V
V_O	DC Output Voltage	$–0.5 \le V_O \le V_{CC} + 0.5$	Note 1.	V
I_{IK}	DC Input Diode Current	–50	$V_I < GND$	mA
I_{OK}	DC Output Diode Current	–50	$V_O < GND$	mA
		+50	$V_O > V_{CC}$	mA
I_O	DC Output Source/Sink Current	±50		mA
I_{CC}	DC Supply Current Per Supply Pin	±100		mA
I_{GND}	DC Ground Current Per Ground Pin	±100		mA
T_{STG}	Storage Temperature Range	–65 to +150		°C

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute–maximum–rated conditions is not implied.

1. Output in HIGH or LOW State. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Typ	Max	Unit
V_{CC}	Supply Voltage	Operating Data Retention Only	2.0 1.5	2.3 to 3.3	3.6 3.6	V
V_I	Input Voltage		0		5.5	V
V_O	Output Voltage	(HIGH or LOW State)	0		V_{CC}	V
I_{OH}	HIGH Level Output Current	V_{CC}= 3.0V–3.6V V_{CC}= 2.7V–3.0V V_{CC}= 2.3V–2.7V			–24 –12 –8	mA
I_{OL}	LOW Level Output Current	V_{CC}= 3.0V–3.6V V_{CC}= 2.7V–3.0V V_{CC}= 2.3V–2.7V			+24 +12 +8	mA
T_A	Operating Free–Air Temperature		–40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V_{IN} from 0.8V to 2.0V, V_{CC} = 3.0V		0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Condition	T_A = –40°C to +85°C		Unit
			Min	Max	
V_{IH}	Minimum HIGH Level Input Voltage (Note 1.)	$2.3V \leq V_{CC} < 2.7V$ $2.7V \leq V_{CC} < 3.0V$ $3.0V \leq V_{CC} < 3.6V$ $4.5V \leq V_{CC} \leq 5.5V$	1.7 2.0 2.0 0.7 x V_{CC}		V
V_{IL}	Maximum LOW Level Input Voltage (Note 1.)	$2.3V \leq V_{CC} < 2.7V$ $2.7V \leq V_{CC} < 3.0V$ $3.0V \leq V_{CC} < 3.6V$ $4.5V \leq V_{CC} \leq 5.5V$		0.7 0.8 0.8 0.3 x V_{CC}	V
V_{OL}	Maximum LOW Level Output Voltage	$2.3V \leq V_{CC} \leq 3.6V$, I_{OL}= 100μA V_{CC}= 2.3V, I_{OL}= 8**m**A V_{CC}= 2.7V, I_{OL}= 12**m**A V_{CC}= 3.0V, I_{OL}= 16**m**A V_{CC}= 3.0V, I_{OL}= 24**m**A V_{CC}= 4.5V, I_{OL}= 32**m**A		0.2 0.6 0.4 0.4 0.55 0.55	V
I_I	Maximum Input Leakage Current	$2.3V \leq V_{CC} \leq 3.6V$, $0V \leq V_I \leq 5.5V$		±5.0	μA
I_{OFF}	Power–Off Leakage Current	V_{CC}= 0V, V_O or V_I= 5.5V		10.0	μA
I_{CC}	Maximum Quiescent Supply Current	$2.3V \leq V_{CC} \leq 3.6V$, V_I= V_{CC} or GND $2.3V \leq V_{CC} \leq 3.6V$, $3.6V \leq V_I \leq 5.5V$		10 ±10.0	μA
ΔI_{CC}	Increase in I_{CC} per Input	$2.3V \leq V_{CC} \leq 3.6V$ $4.5V \leq V_{CC} \leq 5.5V$		500 1	μA mA

1. These values of V_I are used to test DC electrical characteristics only.

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Limits								Unit
		T_A= –40°C to +85°C								
		V_{CC}= 4.5V to 5.5V		V_{CC}= 3.0V to 3.6V		V_{CC}= 2.7V		V_{CC}= 3.0V to 3.6V		
		C_L= 50pF		C_L= 50pF		C_L= 50pF		C_L= 30pF		
		Min	Max	Min	Max	Min	Max	Min	Max	
t_{PLZ}	Propagation Delay	0.5	3.0	0.8	3.7	1.0	4.4	0.8	3.8	ns
t_{PZL}	Input to Output	0.5	3.0	0.8	3.7	1.0	4.4	0.8	3.8	ns

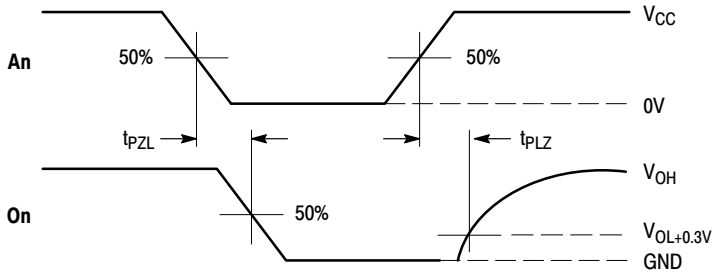
DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Characteristic	Condition	T_A = +25°C			Unit
			Min	Typ	Max	
V_{OLP}	Dynamic LOW Peak Voltage (Note 1.)	V_{CC} = 3.3V, C_L = 50pF, V_{IH} = 3.3V, V_{IL} = 0V V_{CC} = 2.5V, C_L = 30pF, V_{IH} = 2.5V, V_{IL} = 0V		0.9 0.7		V
V_{OLV}	Dynamic LOW Valley Voltage (Note 1.)	V_{CC} = 3.3V, C_L = 50pF, V_{IH} = 3.3V, V_{IL} = 0V V_{CC} = 2.5V, C_L = 30pF, V_{IH} = 2.5V, V_{IL} = 0V		–0.8 –0.6		V

1. Number of outputs defined as “n”. Measured with “n–1” outputs switching from HIGH–to–LOW or LOW–to–HIGH. The remaining output is measured in the LOW state.

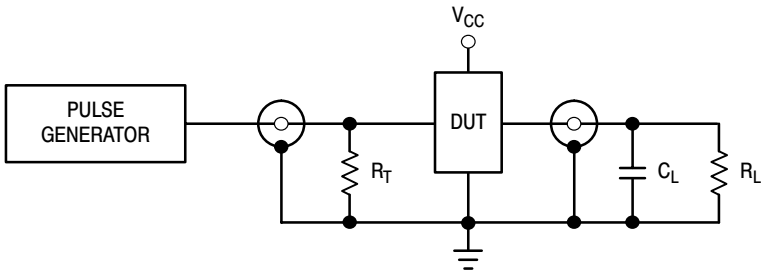
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	V_{CC} = 3.3V, V_I = 0V or V_{CC}	7	pF
C_{OUT}	Output Capacitance	V_{CC} = 3.3V, V_I = 0V or V_{CC}	8	pF
C_{PD}	Power Dissipation Capacitance	10MHz, V_{CC} = 3.3V, V_I = 0V or V_{CC}	25	pF



PROPAGATION DELAYS
$t_R = t_F$ = 2.5ns, 10% to 90%; f = 1MHz; t_W = 500ns

Figure 2. Figure 1. AC Waveforms

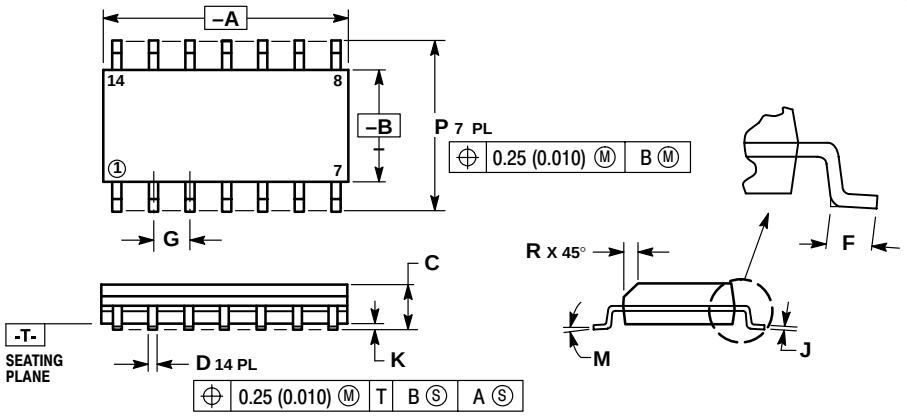


C_L = 50pF or equivalent (Includes jig and probe capacitance)
$R_L = R_1$ = 500Ω or equivalent
$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

Figure 2. Test Circuit

PACKAGE DIMENSIONS

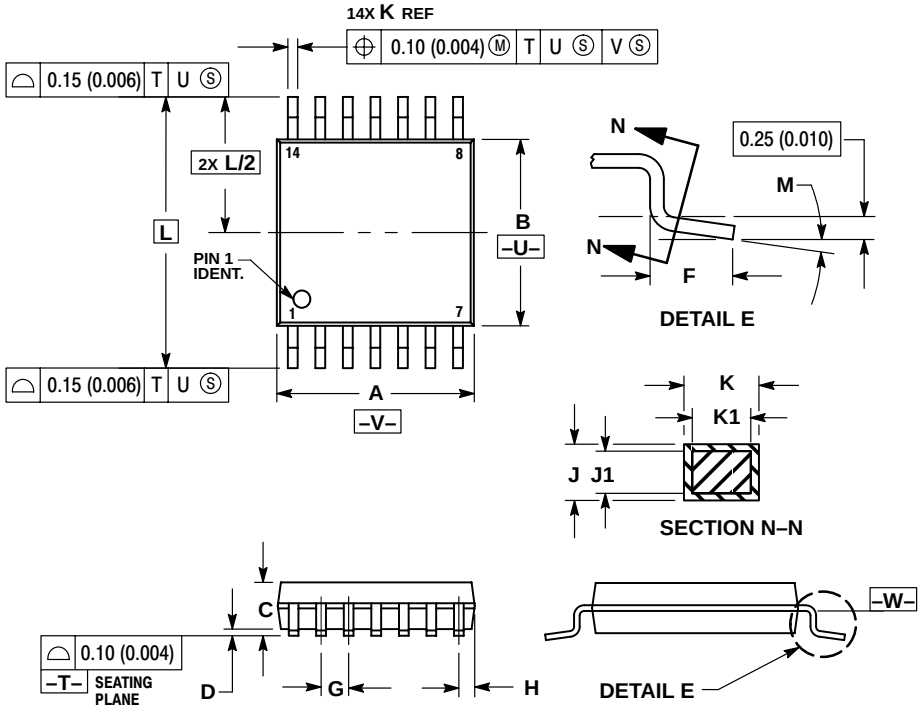
SOIC–14
D SUFFIX
CASE 751A–03
ISSUE F



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

TSSOP–14
DT SUFFIX
CASE 948G–01
ISSUE O

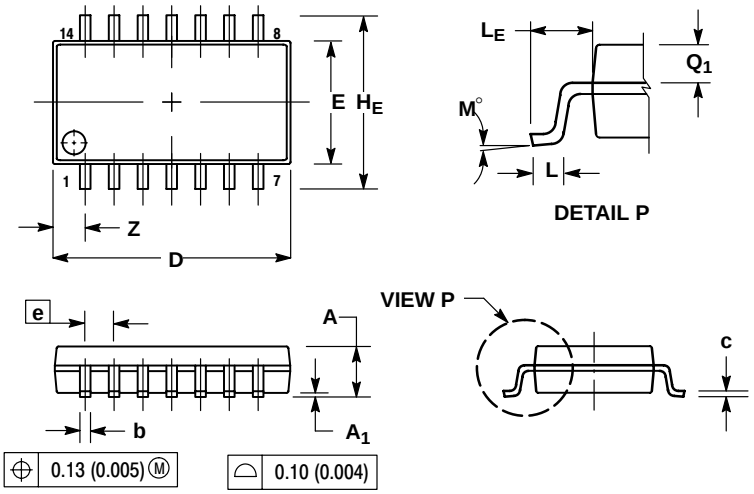


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

PACKAGE DIMENSIONS

SOIC EIAJ–14
M SUFFIX
CASE 965–01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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